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(54) MANUFACTURING METHOD OF SEMICONDUCTOR STRUCTURE

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(57)ABSTRACT

The invention provides a manufacturing method of a semiconductor structure, the method includes providing a substrate, forming two shallow trench isolation structures in the substrate. A first region, a second region and a third region are defined between the two shallow trench isolation structures, and the second region is located between the first region and the third region. Next, an oxide layer is formed in the first region, the second region and the third region, and the oxide layer directly contacts the two shallow trench isolation structures. The oxide layer in the second region is then removed, and another oxide layer is formed in the first region, the second region and the third region, so that a thick oxide layer is formed in the first and third regions, and a thin oxide layer is formed in the second region.

